

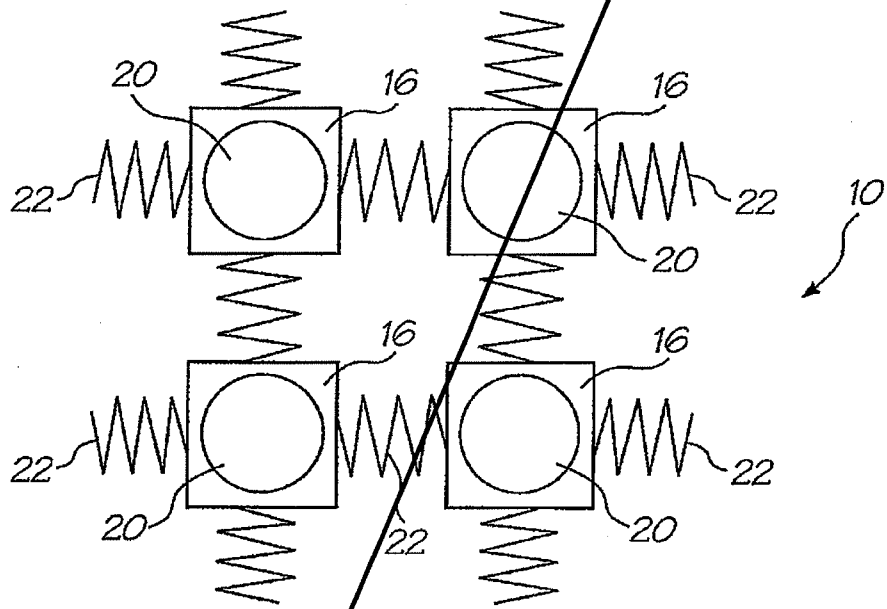
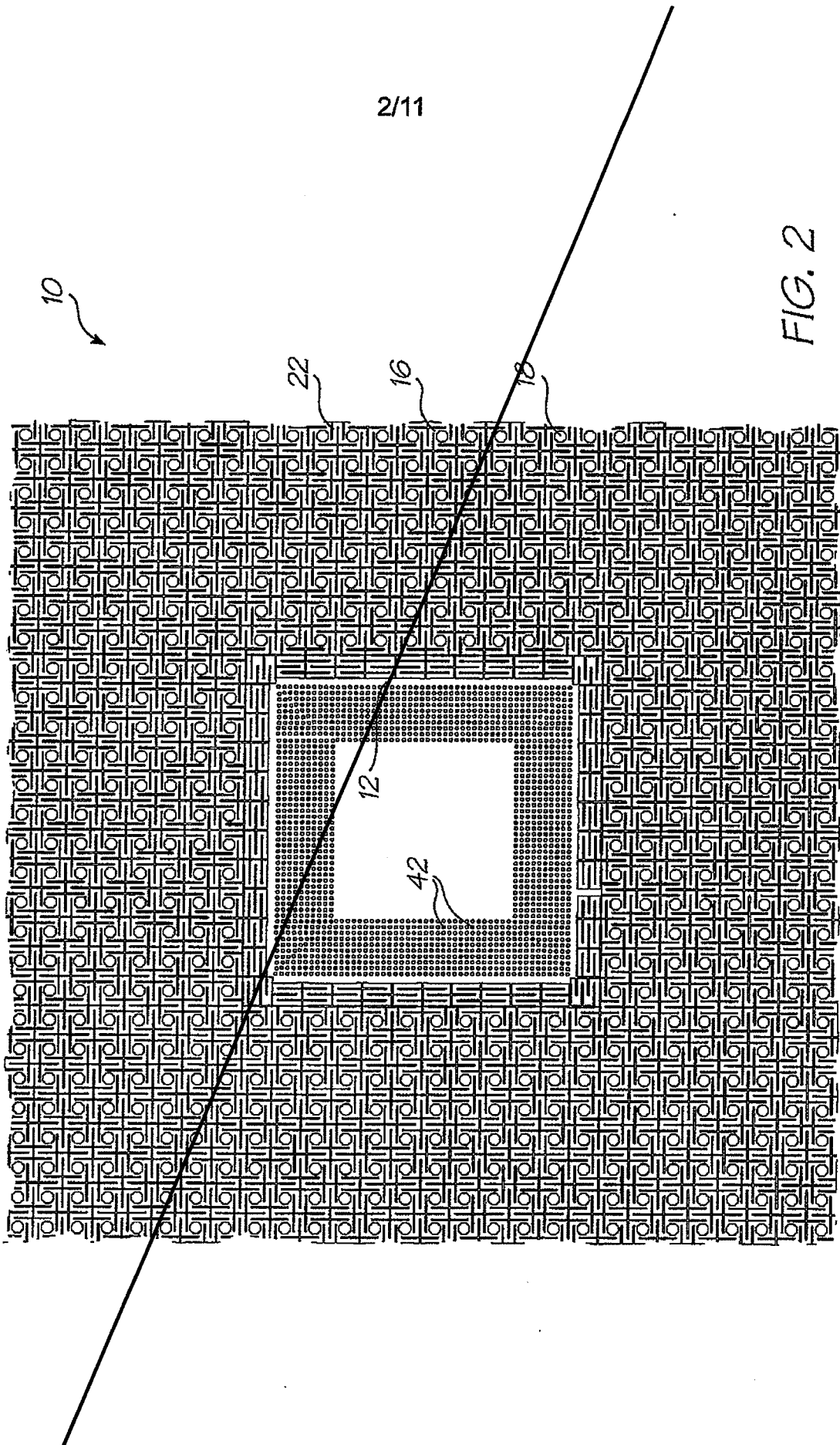


FIG. 1

FIG. 2



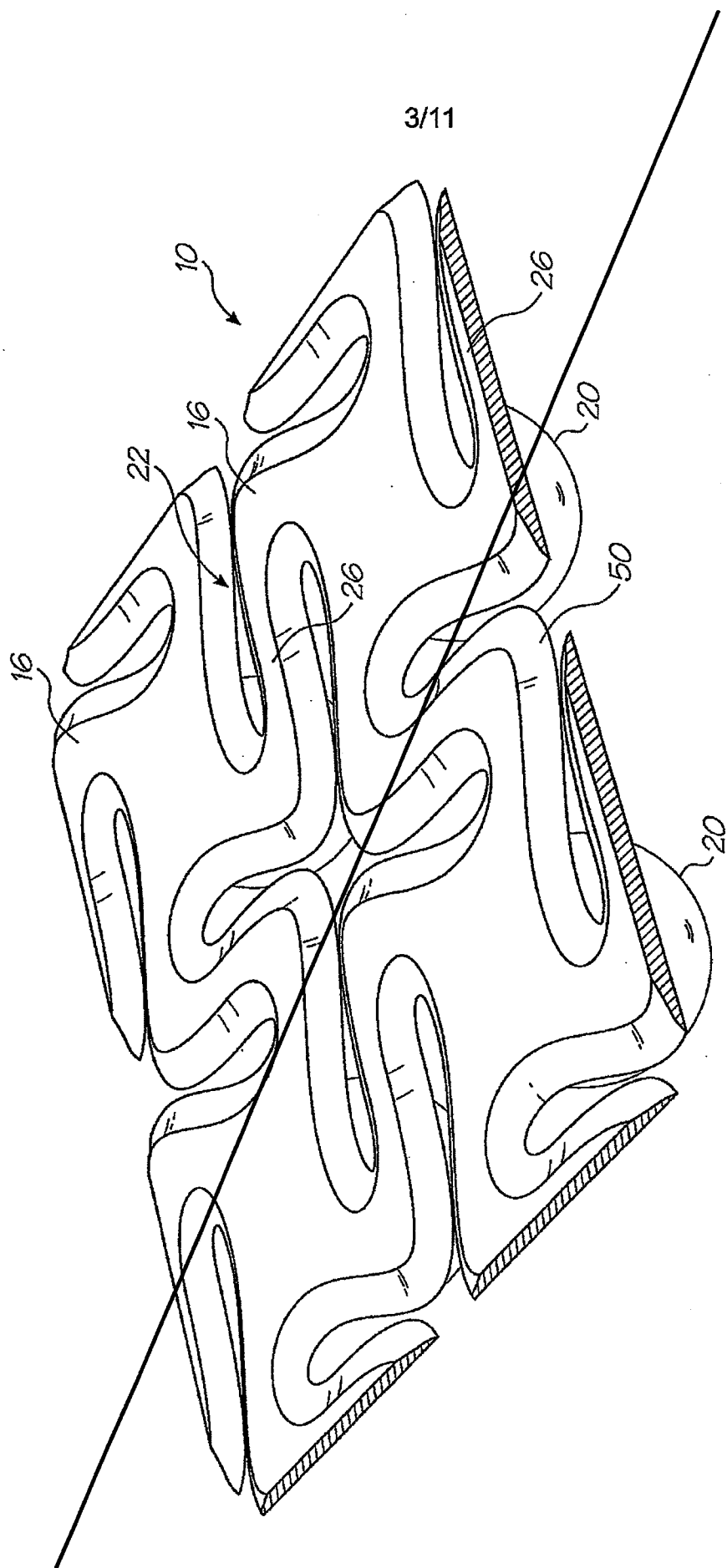


FIG. 3

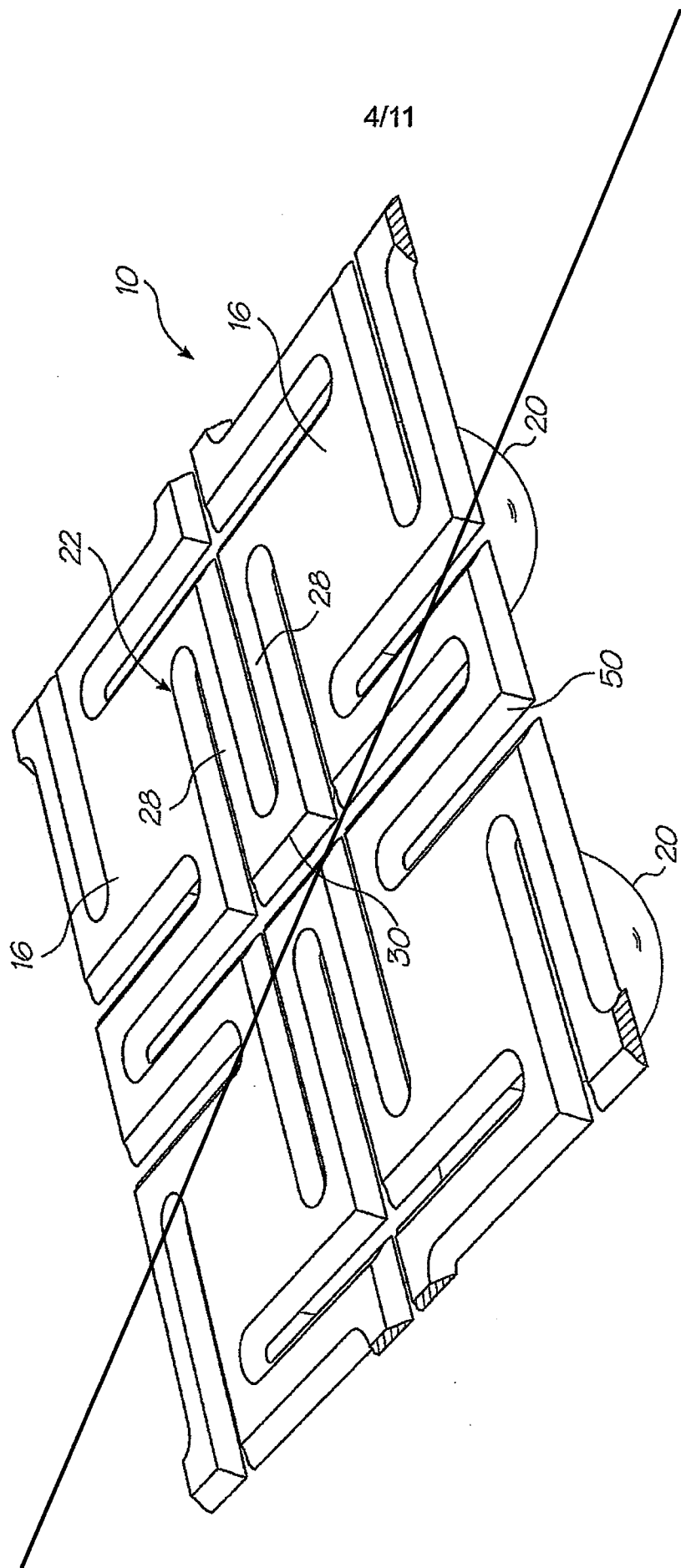


FIG. 4

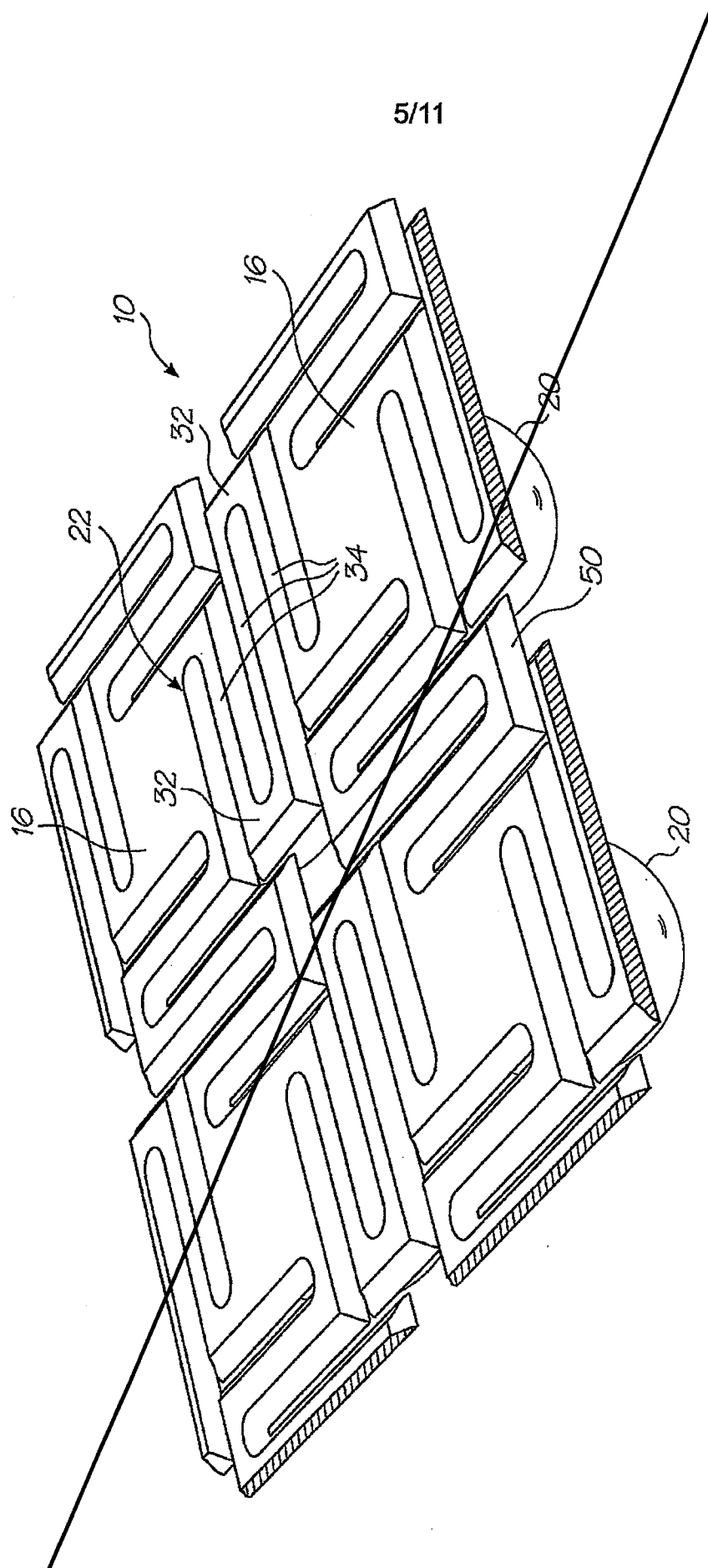


FIG. 5

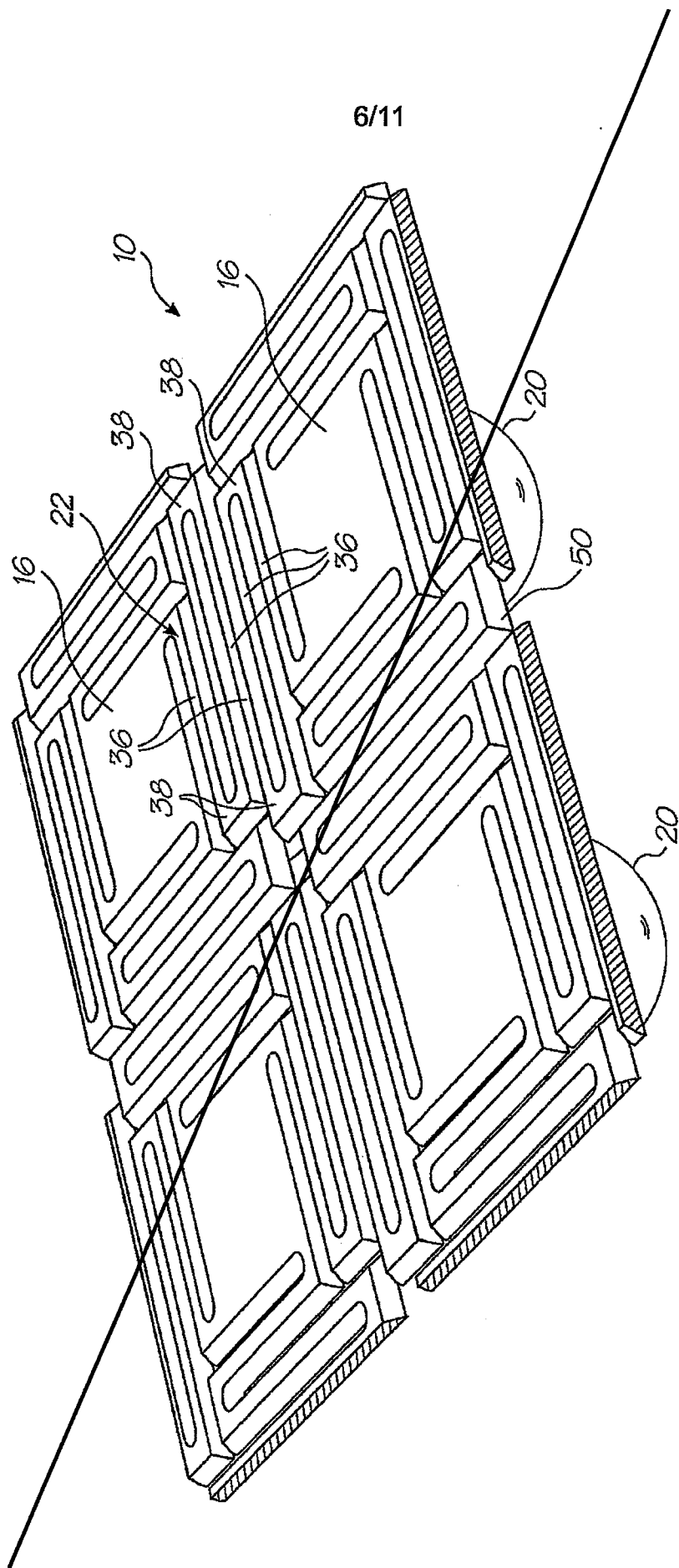


FIG. 6

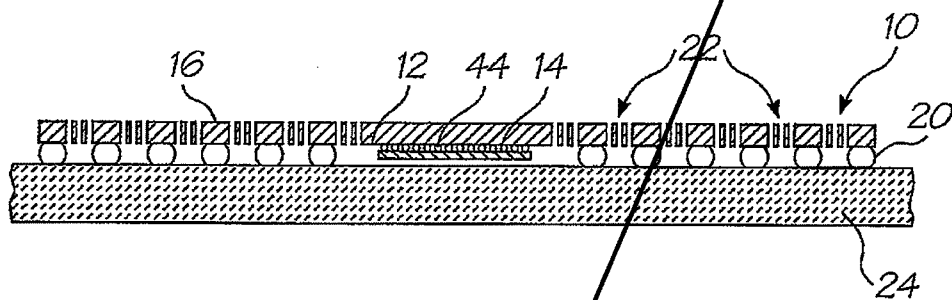


FIG. 7

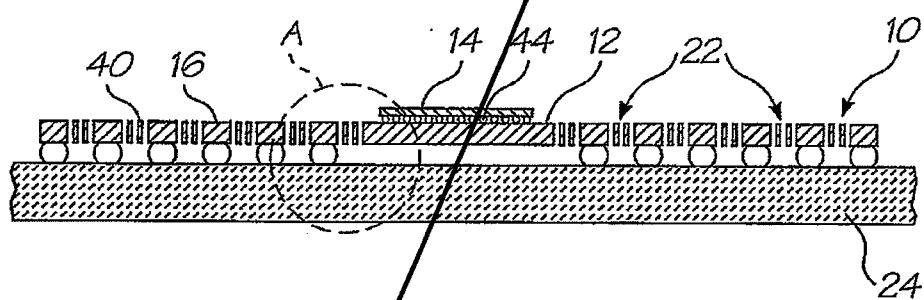


FIG. 8

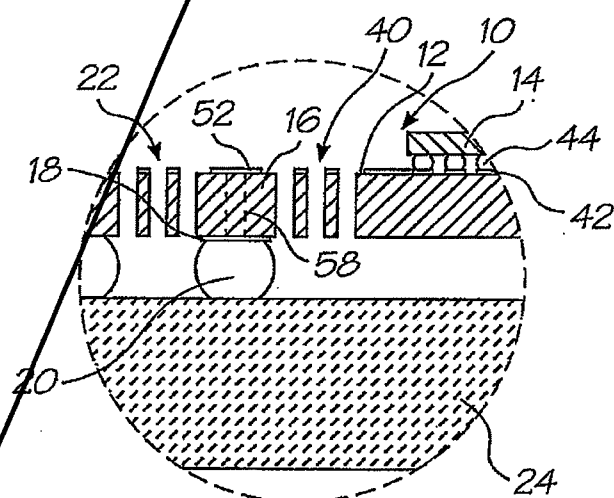


FIG. 9

8/11

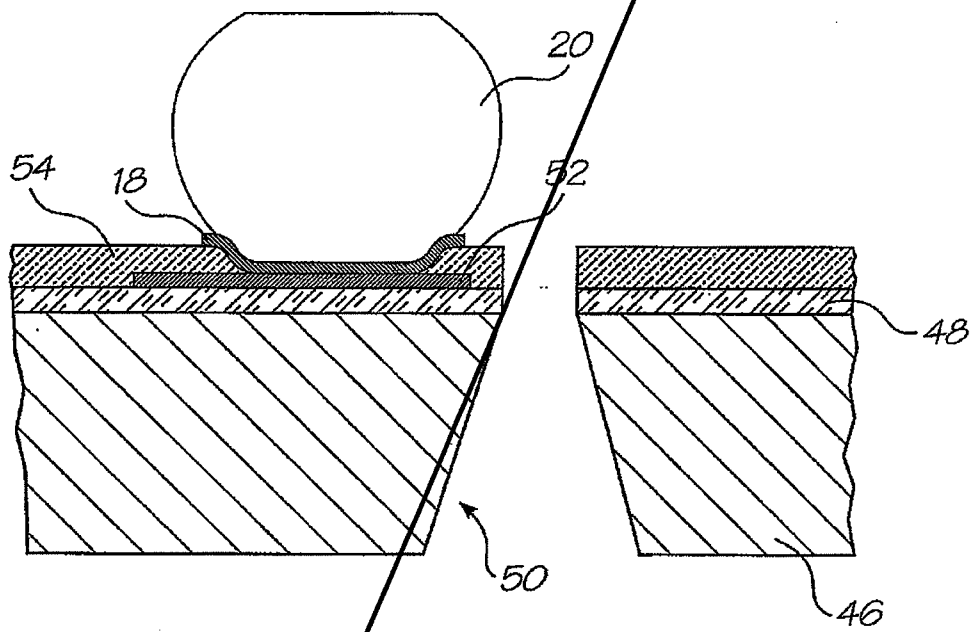
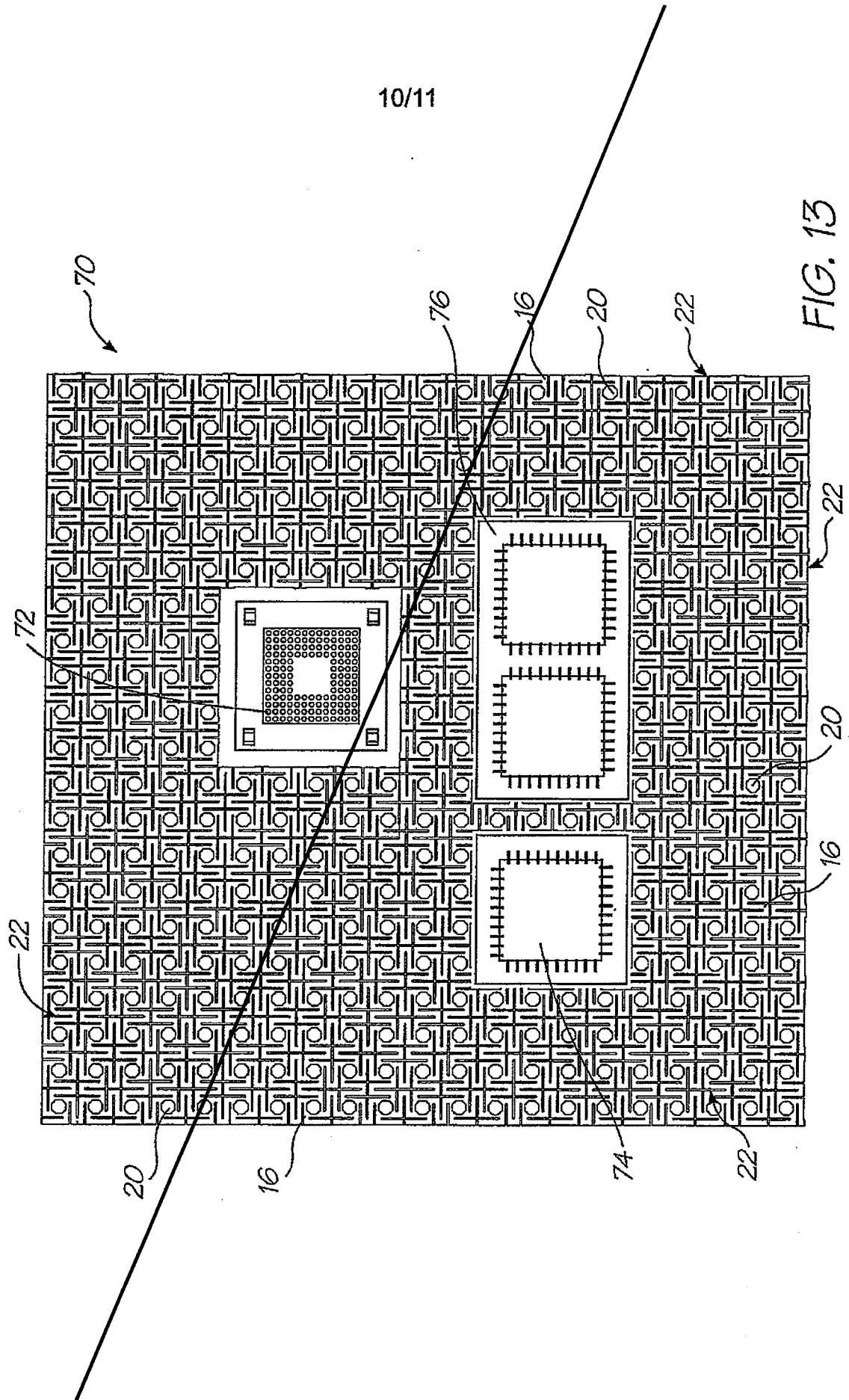


FIG. 10

This cross-sectional view shows a substrate 16 with a series of circular features 20. A central gate structure 14 is formed on the substrate, consisting of a gate dielectric 60 and a gate electrode 62. A gate contact 66 is located on the side of the gate electrode. A source/drain region 12 is formed on the substrate, and a source/drain contact 22 is located on the side of the source/drain region. A diagonal line 40 indicates a cross-section through the device.

FIG. 12



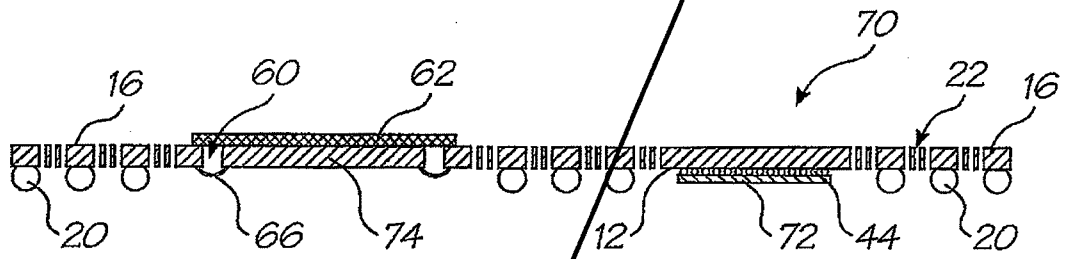


FIG. 14

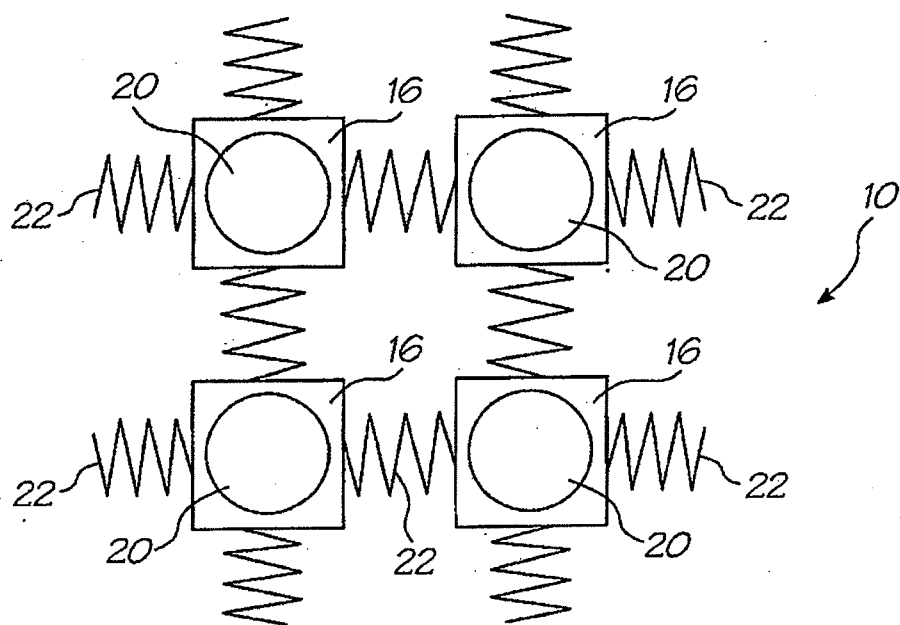


FIG. 1

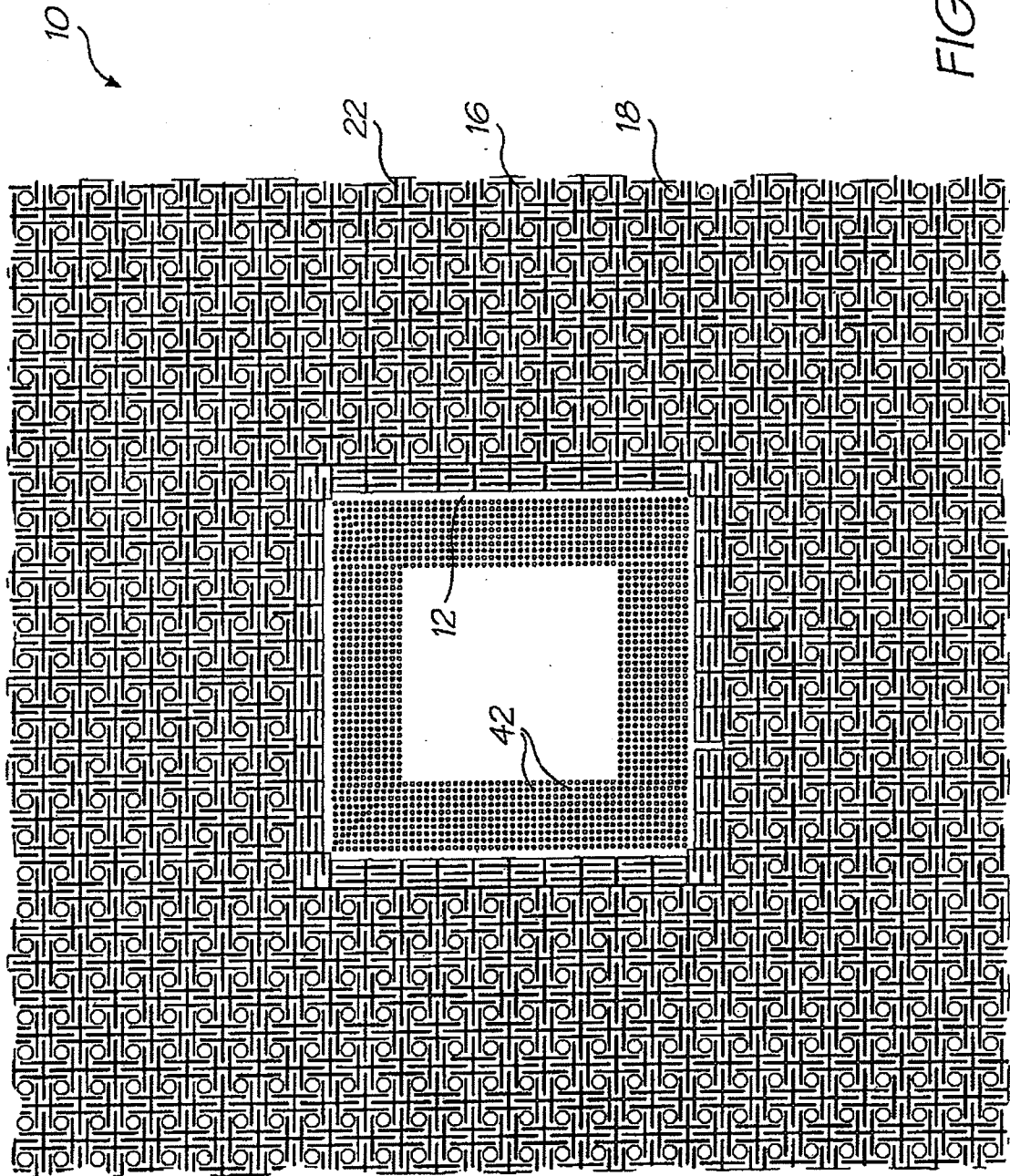


FIG. 2

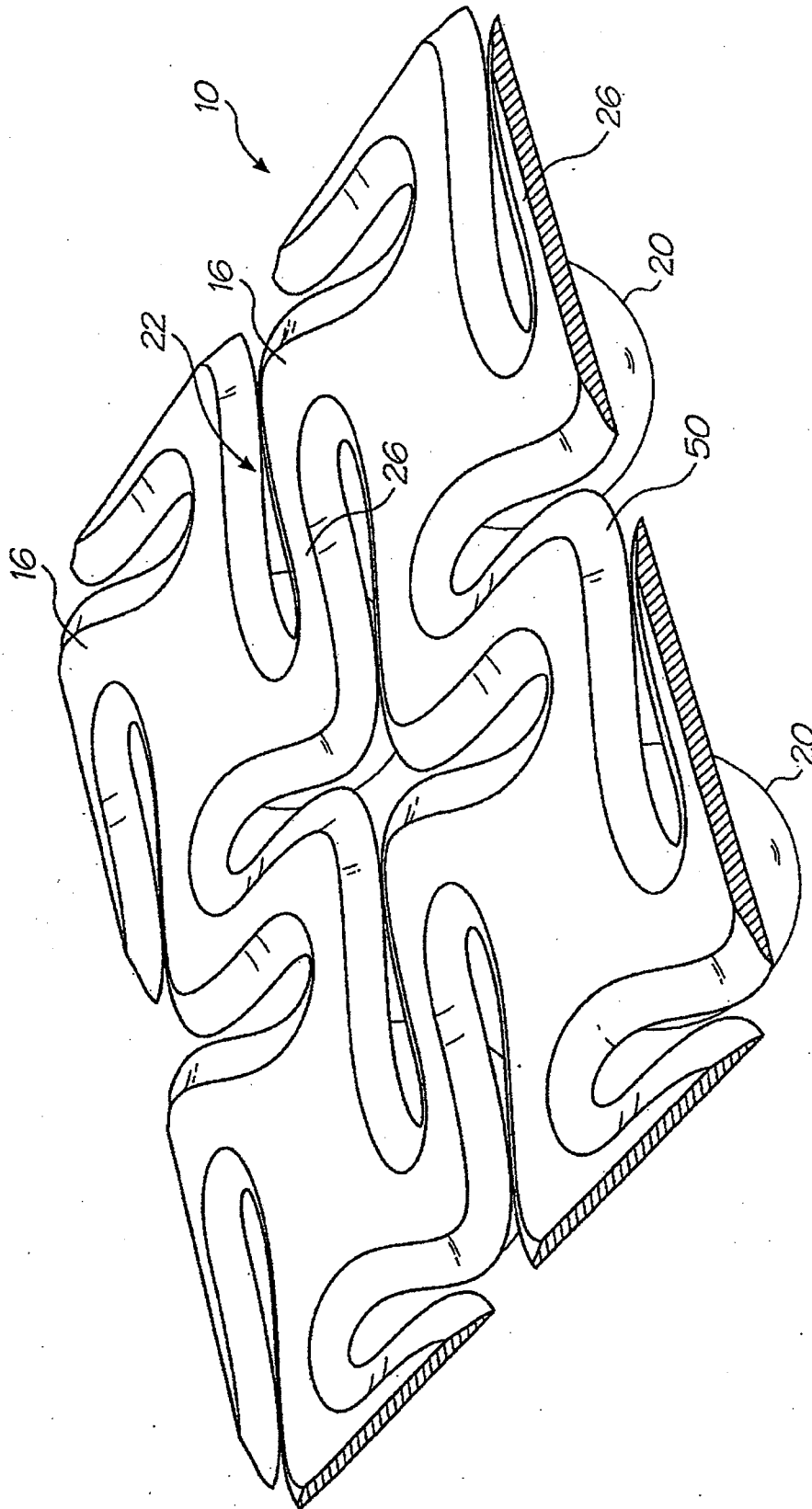


FIG. 3

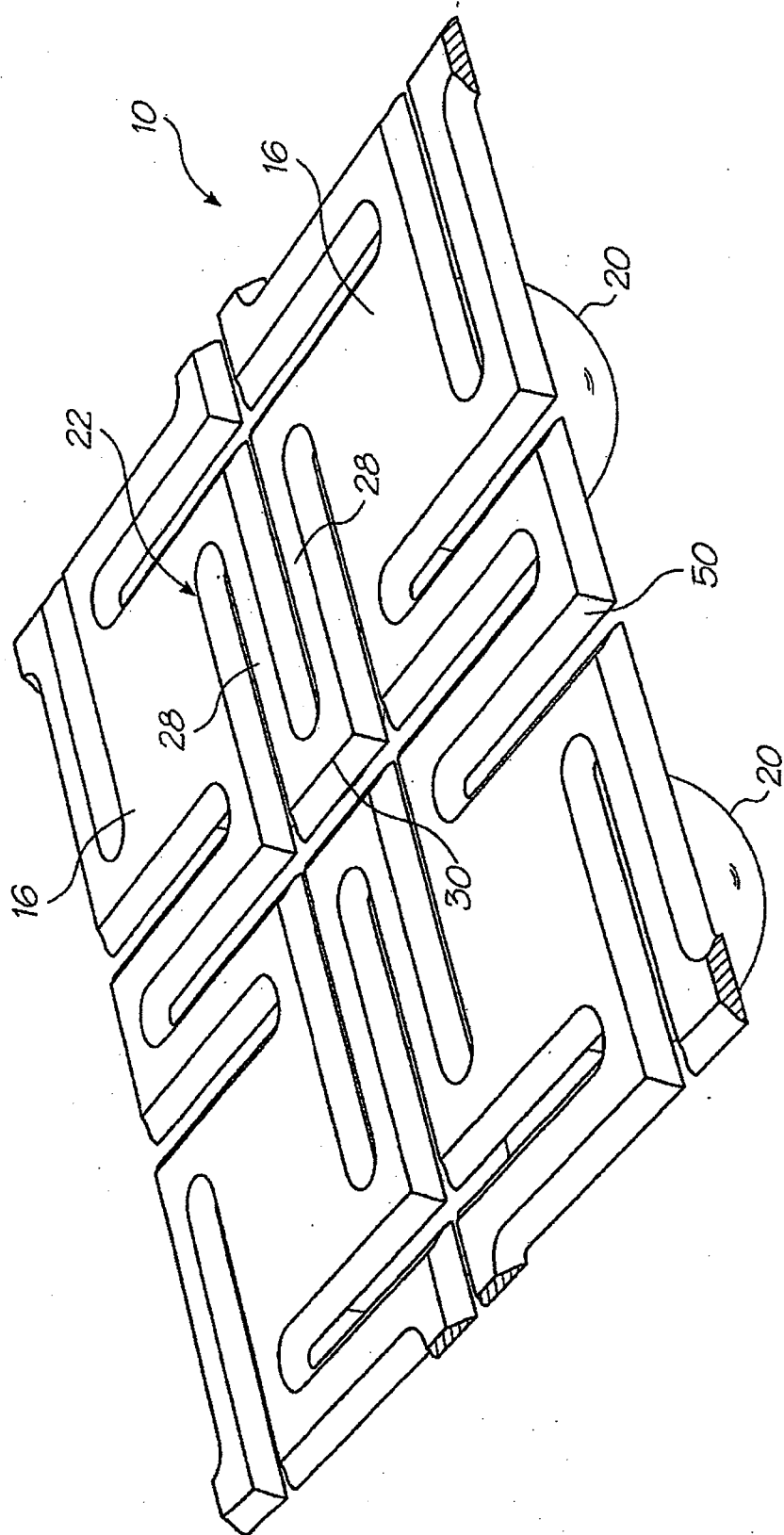


FIG. 4

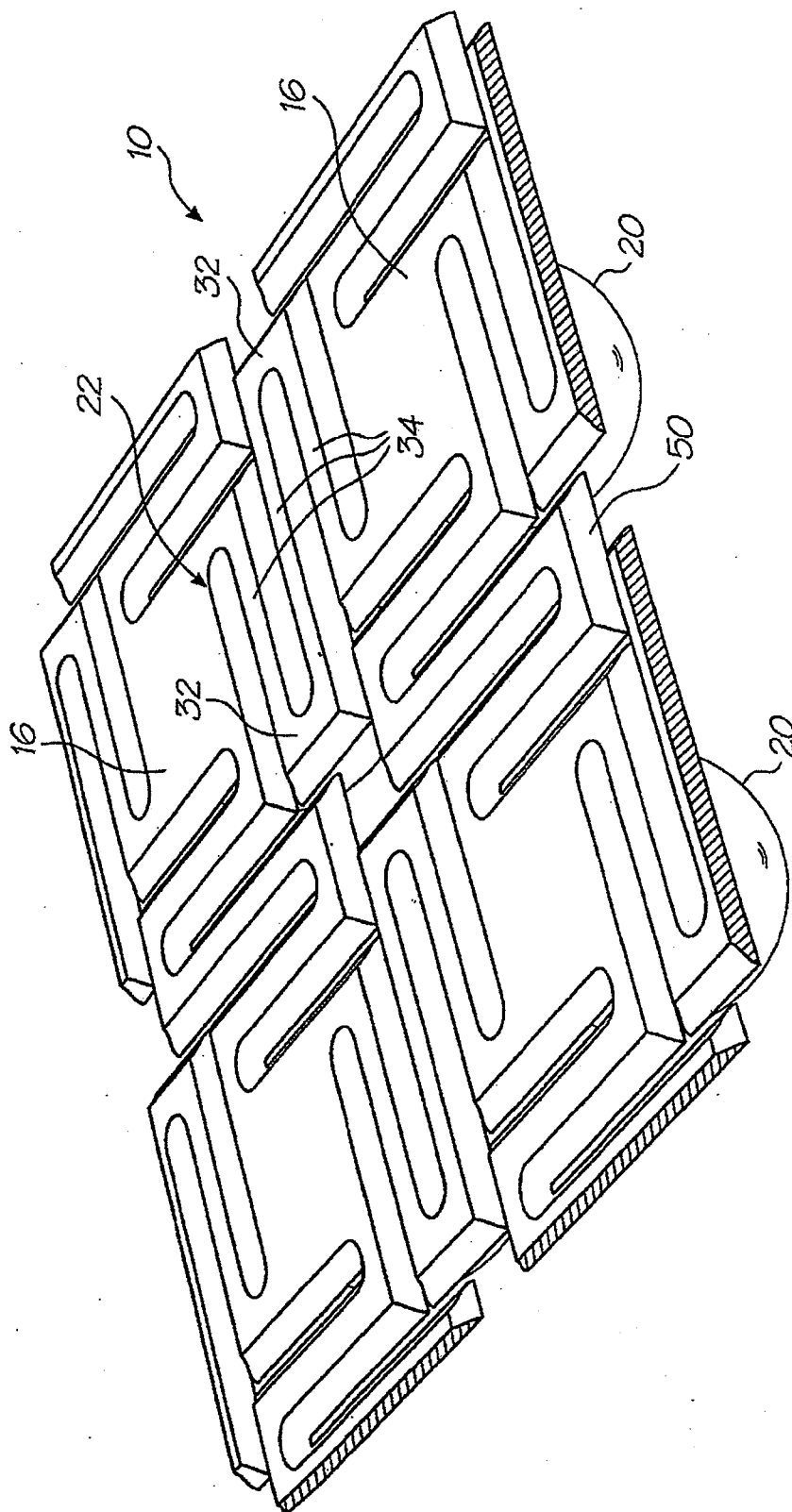


FIG. 5



FIG. 6

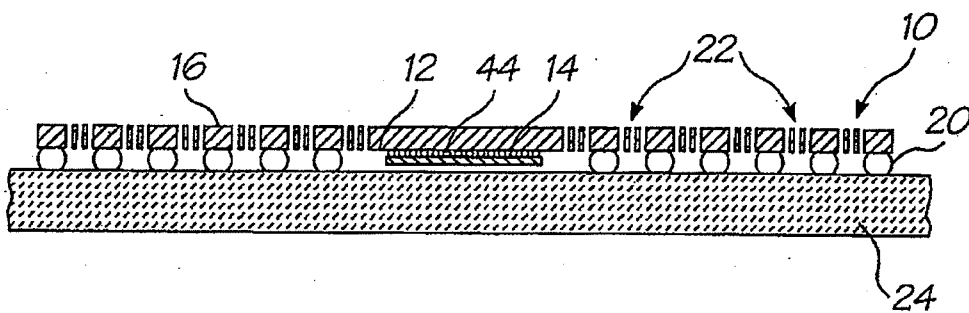


FIG. 7

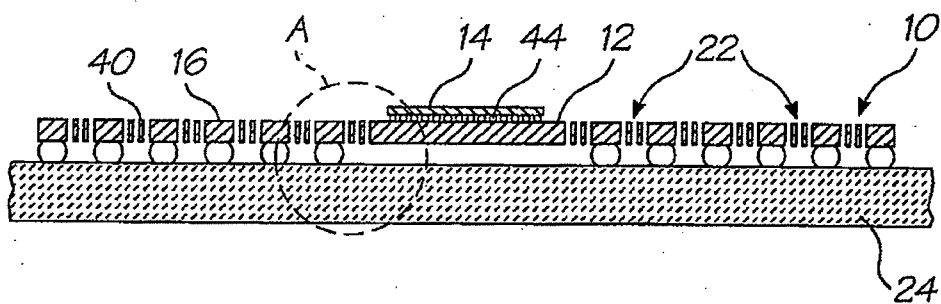


FIG. 8

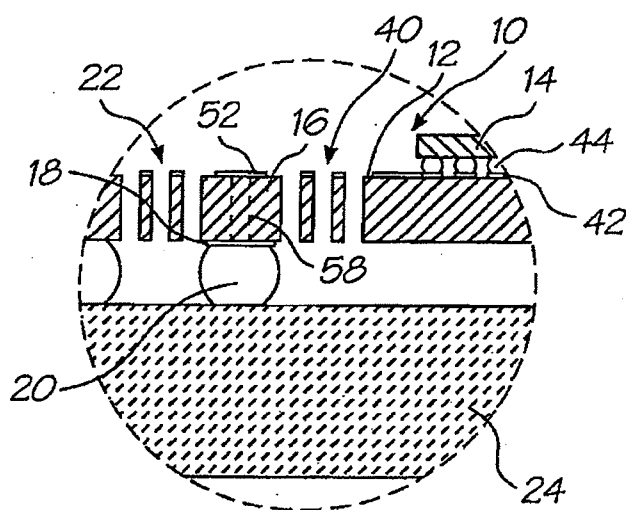


FIG. 9

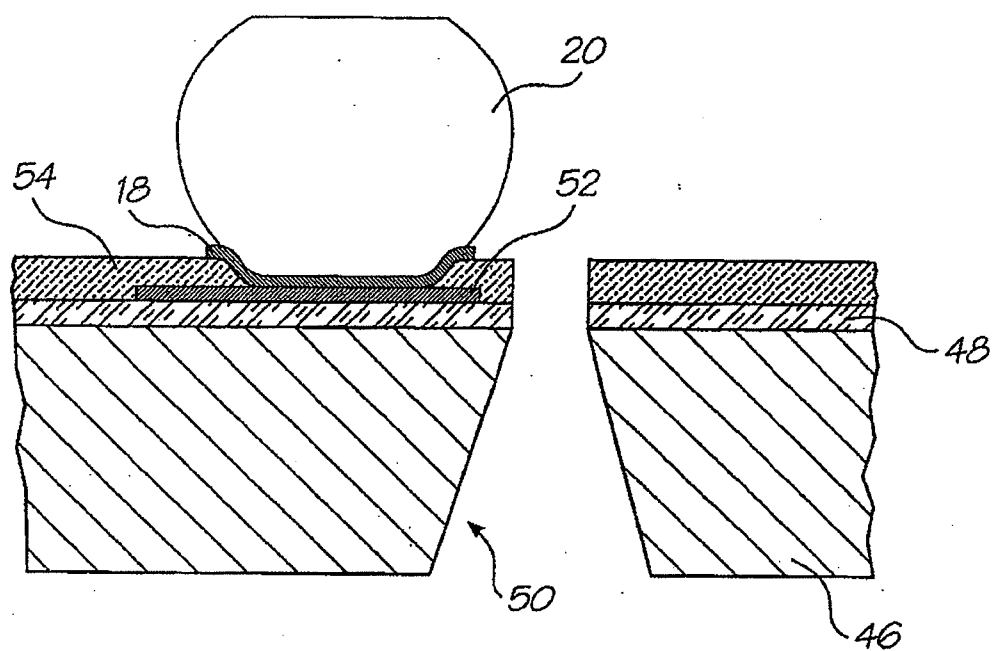


FIG. 10

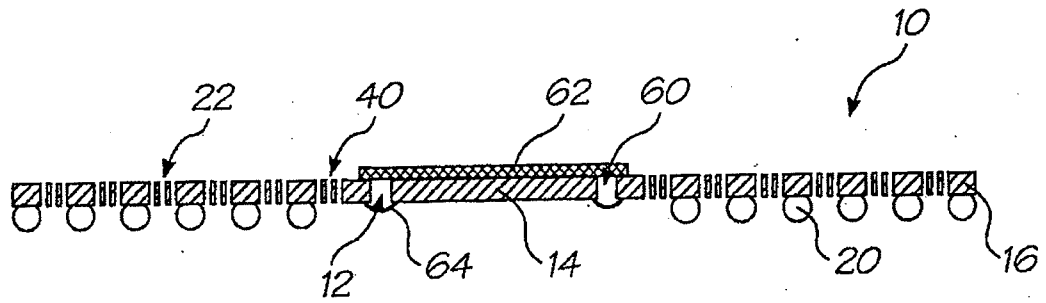


FIG. 11

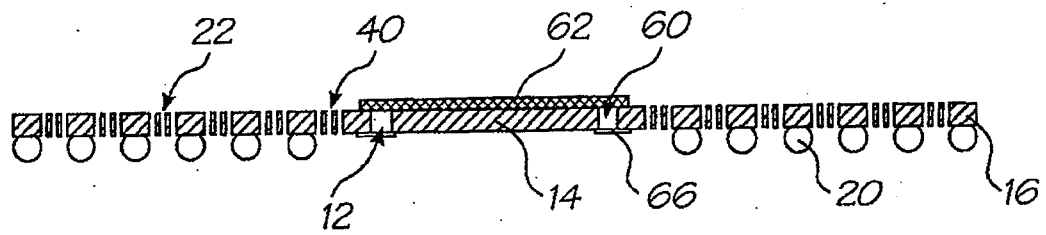


FIG. 12

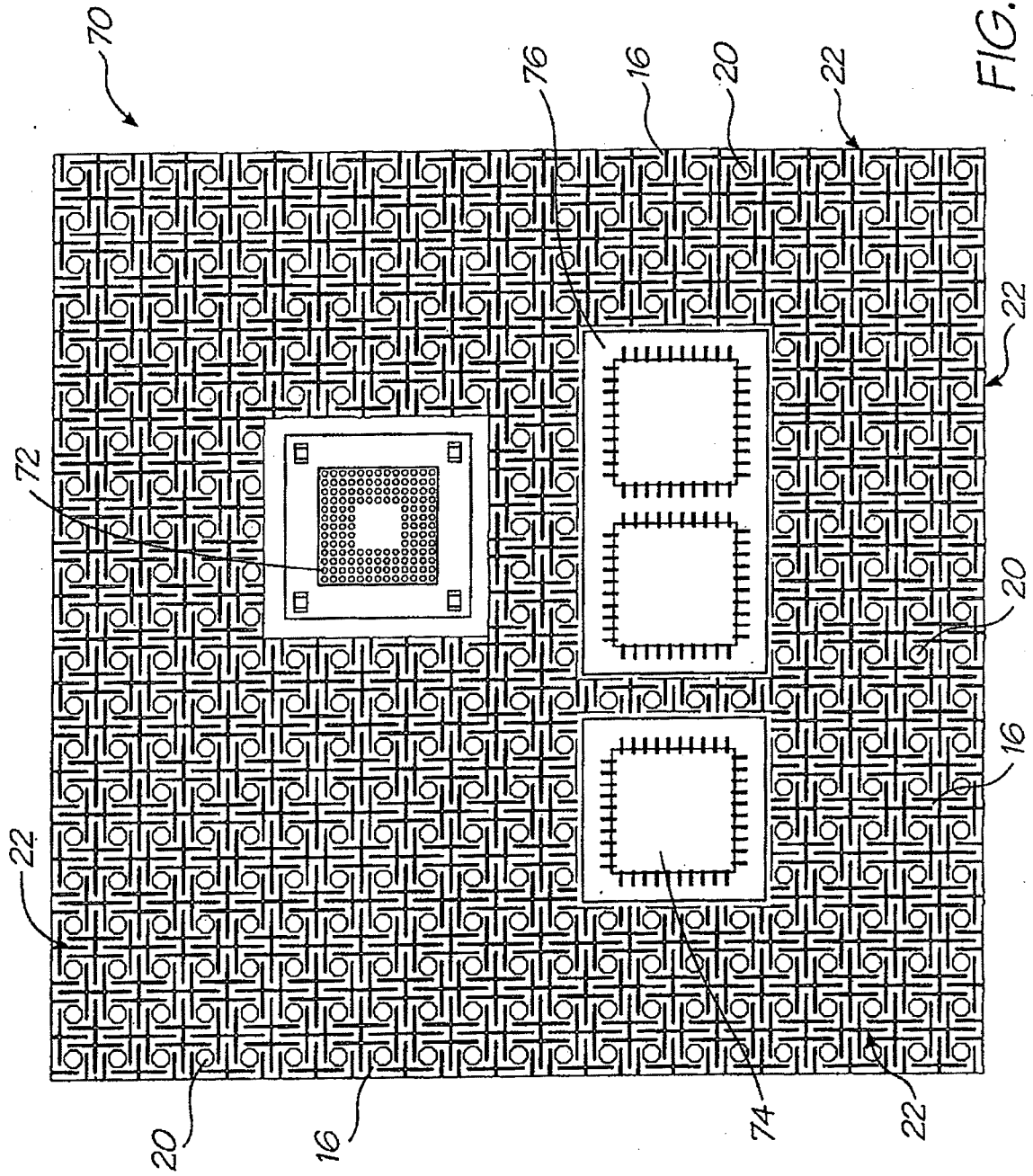


FIG. 13

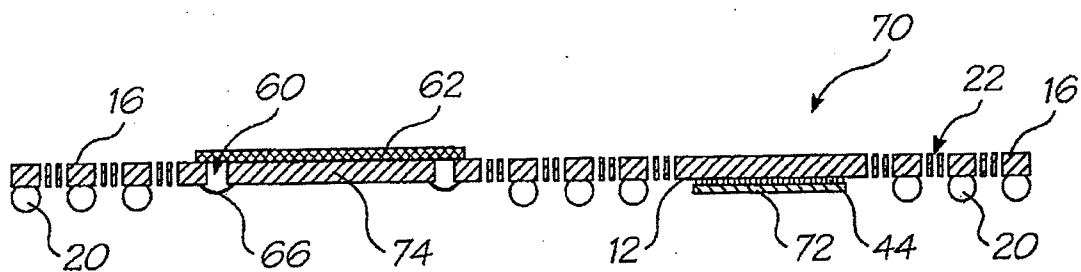


FIG. 14